

SAMYANG ELECTRONICS MBR1020CT --- MBR10200CT

SCHOTTKY BARRIER RECTIFIER

FEATURES

- \bigotimes Metal-semiconductor junction with guard ring
- \bigcirc Epitaxial construction
- \bigotimes Low forward voltage drop,low switching losses
- \bigcirc High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- \bigcirc The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- - MIL-STD-202,Method 208
- ◇Polarity: As marked
- ♦ Weight: 0.08ounces, 2.24 grams
- ♦ Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

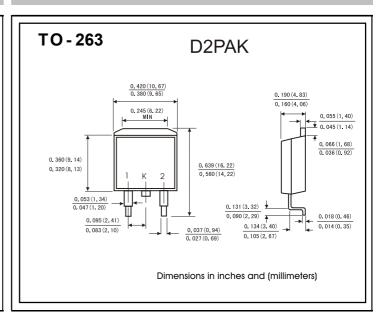
		Symbols	MBR 1020CT	MBR 1030CT	MBR 1040CT	MBR 1050CT	MBR 1060CT	MBR 1080CT	^{МВR} 10100СТ	MBR 10150CT	MBR 10200CT	Units
Maximum repetitive peak reverse voltage		Vrrm	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage		Vrms	14	21	28	35	42	56	70	105	140	Volts
Maximum DC blocking voltage		Vdc	20	30	40	50	60	80	100	150	200	Volts
Maximum average forward rectified current(see Fig.1)	Per leg Total device	I(AV)	5.0 10.0							Amps		
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		IFSM	150.0								Amps	
Maximum instantaneous forward voltage at 10.0 A(Note 1)		VF	0. 60		C).75	0.85		0.90	0.95	Volts	
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1)	^e T _∧ =25°C	1-	0.2									•
	T _A =125°C	R		15		50						mA
Typical thermal resistance (Note 2)		R _θ JC	2.5									°C/W
Operating junction temperature range		TJ	-65 to+150								C	
Storage temperature range		Tstg	-65 to+150									°C

NOTE: 1. Pulse test:300us pulse width,1% duty cycle.

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3. Thermal resistance junction to ambient

VOLTAGE RANGE: 20 --- 200 V CURRENT: 10.0A



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RATINGS AND CHARACTERISTIC CURVES

